

General Description

The AGM628M1 combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

This device is ideal for load switch and battery protection applications.

Features

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance
- 100% Avalanche tested
- 100% DVDS tested

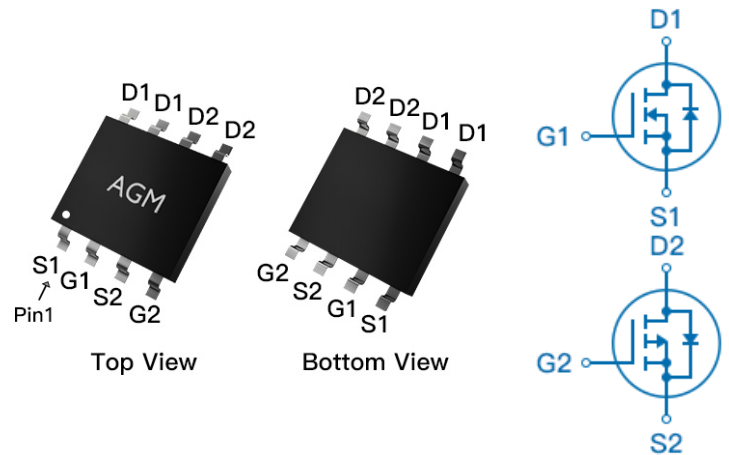
Application

- MB/VGA Vcore
- SMPS 2nd Synchronous Rectifier
- POL application
- BLDC Motor driver

Product Summary

BVDSS	RDSON	ID
60V	27mΩ	6.0A
-60V	70mΩ	-4.2A

SOP8 Pin Configuration



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
AGM628M	AGM628M1	SOP8	330mm	12mm	3000

Table 1. Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$)

Symbol	Parameter	Rating		Units
		N-Ch	P-Ch	
V_{DS}	Drain-Source Voltage ($V_{GS}=0V$)	60	-60	V
V_{GS}	Gate-Source Voltage ($V_{DS}=0V$)	± 20	± 20	V
I_D	Drain Current-Continuous($T_A=25^{\circ}\text{C}$) (Note 1)	6.0	-4.2	A
	Drain Current-Continuous($T_A=100^{\circ}\text{C}$)	4.0	-3.2	A
IDM (pluse)	Drain Current-Pulsed (Note 2)	24	-16.8	A
P_D	Total Power Dissipation($T_A=25^{\circ}\text{C}$)	2.5	2.5	W
EAS	Avalanche energy (Note 3)	20	16	mJ
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 To 150	-55 To 150	$^{\circ}\text{C}$

Table 2. Thermal Characteristic

Symbol	Parameter	Typ	Max	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient (Steady State) ¹	---	50	$^{\circ}\text{C/W}$

Table 3. N- Channel Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BVDSS	Drain-Source Breakdown Voltage	VGS=0V ID=250μA	60	--	--	V
IDSS	Zero Gate Voltage Drain Current	VDS=60V,VGS=0V	--	--	1	μA
IGSS	Gate-Body Leakage Current	VGS=±20V,VDS=0V	--	--	±100	nA
VGS(th)	Gate Threshold Voltage	VDS=VGS,ID=250μA	1.2	1.6	2.2	V
gFS	Forward Transconductance	VDS=5V,ID=5A	--	34	--	S
RDS(on)	Drain-Source On-State Resistance	VGS=10V, ID=6A	--	27	44	mΩ
		VGS=4.5V, ID=5A	--	36	55	mΩ
Dynamic Characteristics						
Ciss	Input Capacitance	VDS=30V,VGS=0V, F=1MHZ	--	866	--	pF
Coss	Output Capacitance		--	42	--	pF
Crss	Reverse Transfer Capacitance		--	38	--	pF
Rg	Gate resistance	VGS=0V, VDS=0V,f=1.0MHz	--	--	--	Ω
Switching Times						
td(on)	Turn-on Delay Time	VGS=10V,VDS=30V, RL=2.5Ω,RGEN=3Ω	--	4.3	--	nS
tr	Turn-on Rise Time		--	15	--	nS
td(off)	Turn-Off Delay Time		--	14.2	--	nS
tf	Turn-Off Fall Time		--	18	--	nS
Qg	Total Gate Charge	VGS=10V, VDS=30V, ID=3A	--	18	--	nC
Qgs	Gate-Source Charge		--	4.1	--	nC
Qgd	Gate-Drain Charge		--	2.4	--	nC
Source-Drain Diode Characteristics						
ISD	Source-Drain Current(Body Diode)		--	--	6.0	A
VSD	Forward on Voltage	VGS=0V,IS=6A	--	--	1.2	V
trr	Reverse Recovery Time	IF=6A , dl/dt=100A/μs , TJ=25°C	--	--	--	ns
Qrr	Reverse Recovery Charge		--	--	--	nc

Notes 1.The maximum current rating is package limited.

Notes 2.Repetitive Rating: Pulse width limited by maximum junction temperature

Notes 3.EAS condition: T_J=25°C

Table 3. P-Channel Electrical Characteristics (TJ=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BVDSS	Drain-Source Breakdown Voltage	VGS=0V ID=-250μA	-60	--	--	V
IDSS	Zero Gate Voltage Drain Current	VDS=-60V,VGS=0V	--	--	-1	μA
IGSS	Gate-Body Leakage Current	VGS=±20V,VDS=0V	--	--	±100	nA
VGS(th)	Gate Threshold Voltage	VDS=VGS,ID=-250μA	-1.2	-1.7	-2.2	V
gFS	Forward Transconductance	VDS=-5V,ID=-2A	--	8.7	--	S
RDS(on)	Drain-Source On-State Resistance	VGS=-10V, ID=-3A	--	70	95	mΩ
		VGS=-4.5V, ID=-2A	--	101	125	mΩ
Dynamic Characteristics						
Ciss	Input Capacitance	VDS=-30V,VGS=0V, F=1MHZ	--	1080	--	pF
Coss	Output Capacitance		--	73	--	pF
Crss	Reverse Transfer Capacitance		--	50	--	pF
Rg	Gate resistance	VGS=0V, VDS=0V,f=1.0MHz	--	15	--	Ω
Switching Times						
td(on)	Turn-on Delay Time	VGS=-10V,VDS=-30V, RGEN=3Ω	--	10	--	nS
tr	Turn-on Rise Time		--	6.0	--	nS
td(off)	Turn-Off Delay Time		--	40	--	nS
tf	Turn-Off Fall Time		--	13	--	nS
Qg	Total Gate Charge	VGS=-10V, VDS=-30V, ID=-3A	--	11	--	nC
Qgs	Gate-Source Charge		--	1.9	--	nC
Qgd	Gate-Drain Charge		--	6.5	--	nC
Source-Drain Diode Characteristics						
ISD	Source-Drain Current(Body Diode)		--	--	-4.2	A
VSD	Forward on Voltage	VGS=0V,IS=-3A	--	--	-1.2	V
trr	Reverse Recovery Time	IF=-3A , dI/dt=100A/μs , TJ=25℃	--	--	--	ns
Qrr	Reverse Recovery Charge		--	--	--	nc

Notes 1.The maximum current rating is package limited.

Notes2.Repetitive Rating: Pulse width limited by maximum junction temperature Notes

3.EAS condition: TJ=25°C

N-Channel Typical Characteristics

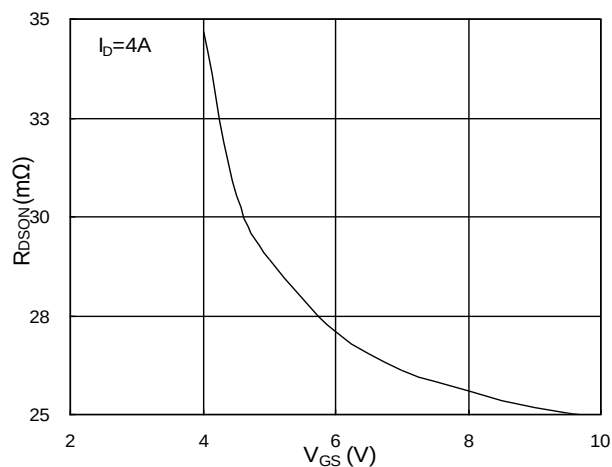
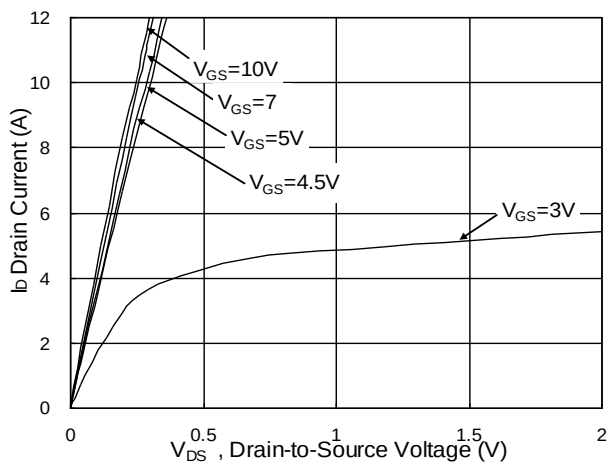


Fig.1 Typical Output Characteristics

Fig.2 On-Resistance v.s Gate-Source

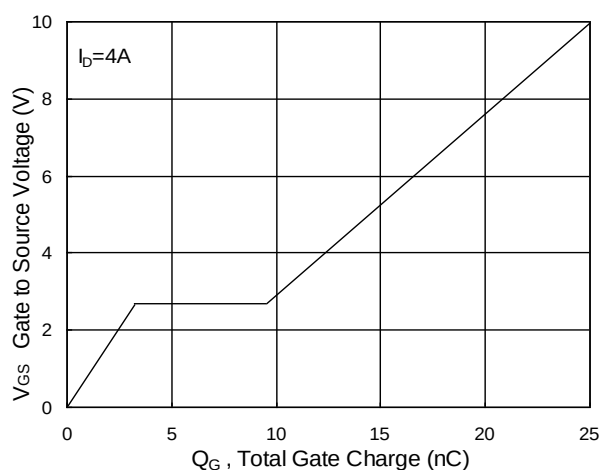
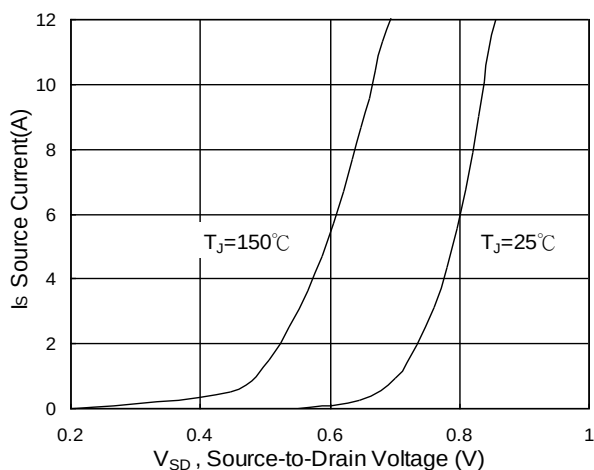


Fig.3 Forward Characteristics of Reverse

Fig.4 Gate-Charge Characteristics

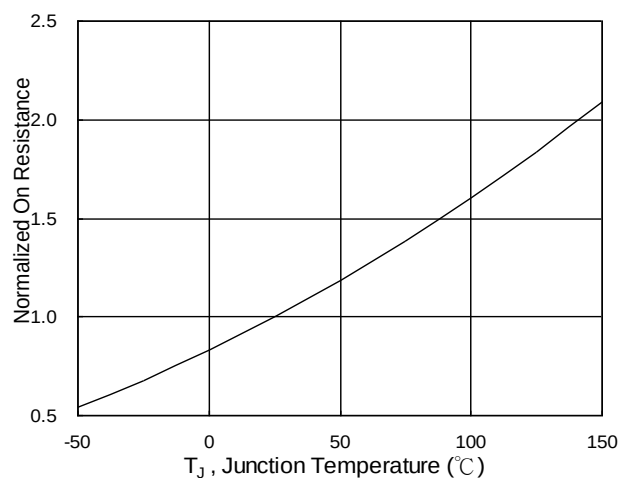
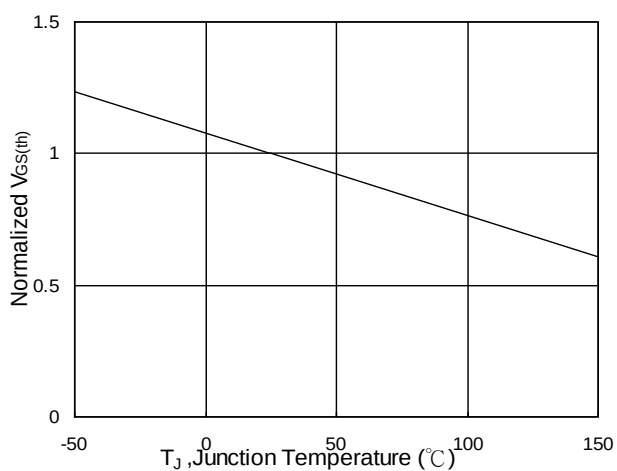


Fig.5 Normalized $V_{GS(th)}$ v.s T_J

Fig.6 Normalized $R_{DS(on)}$ v.s T_J

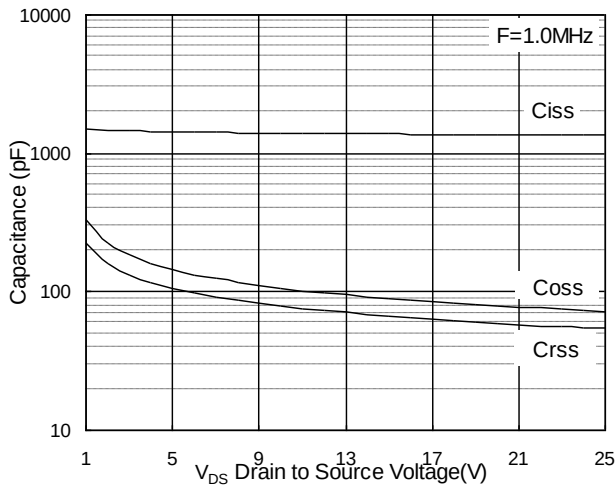


Fig.7 Capacitance

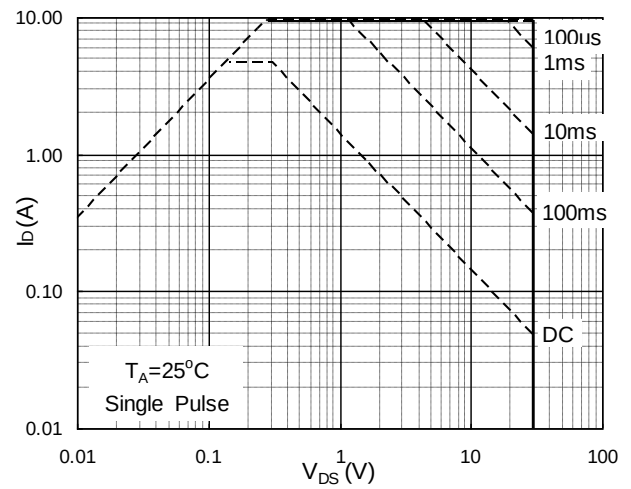


Fig.8 Safe Operating Area

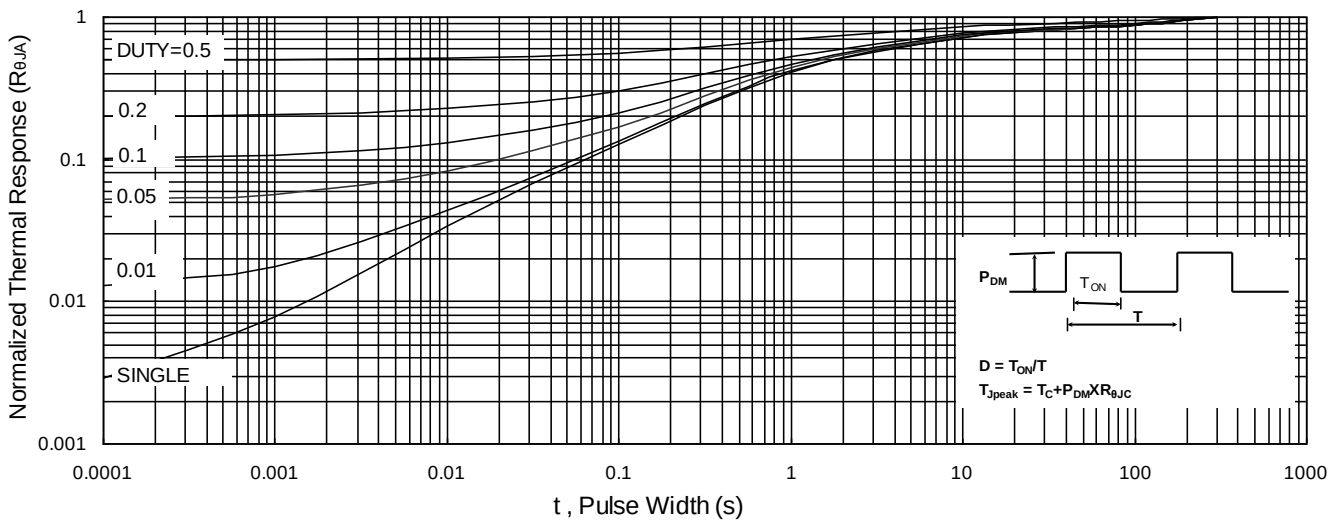


Fig.9 Normalized Maximum Transient Thermal Impedance

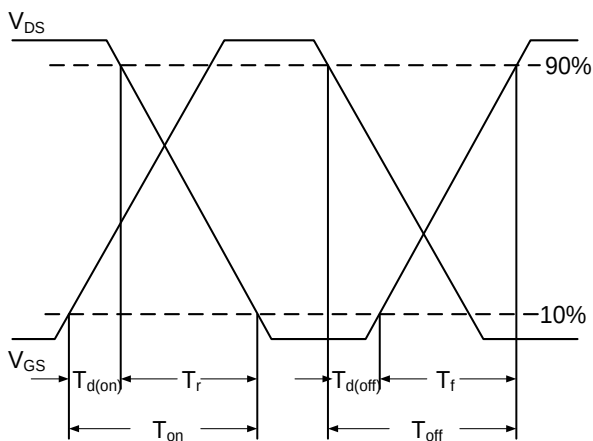


Fig.10 Switching Time Waveform

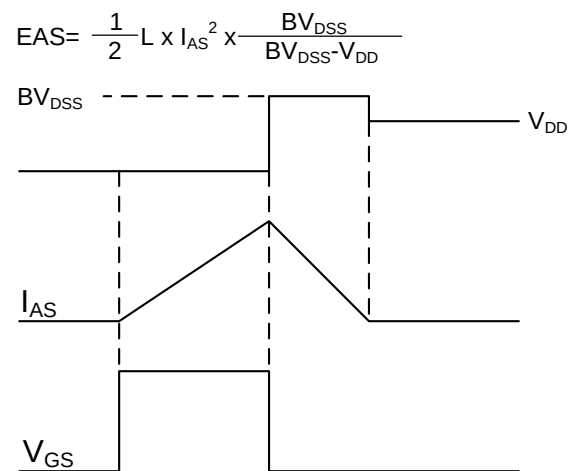


Fig.11 Unclamped Inductive Waveform

P-Channel Typical Characteristics

Typical Characteristics

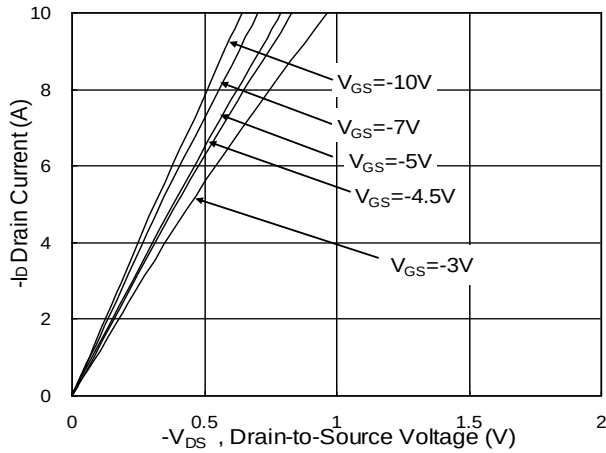


Fig.1 Typical Output Characteristics

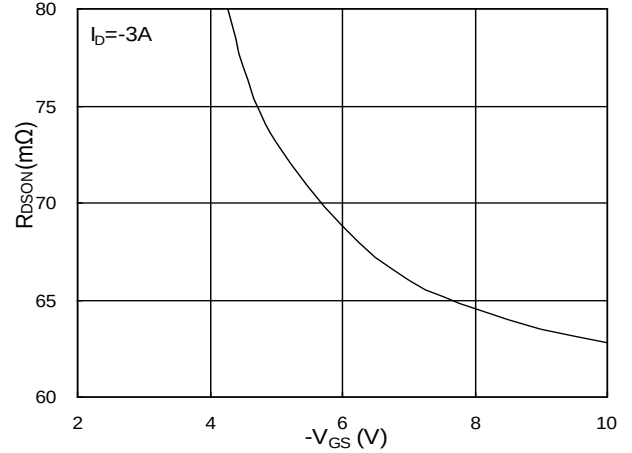


Fig.2 On-Resistance v.s Gate-Source

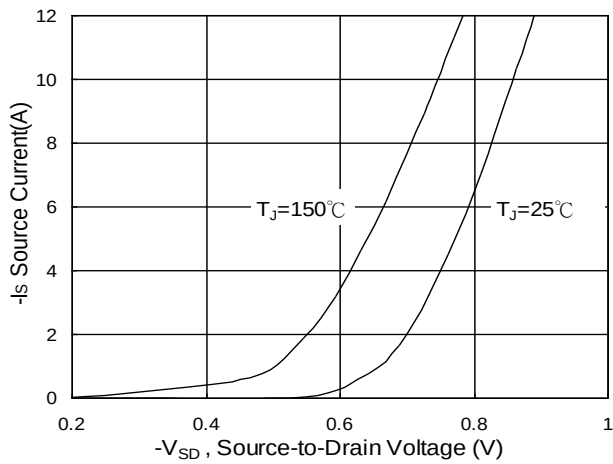


Fig.3 Forward Characteristics of Reverse

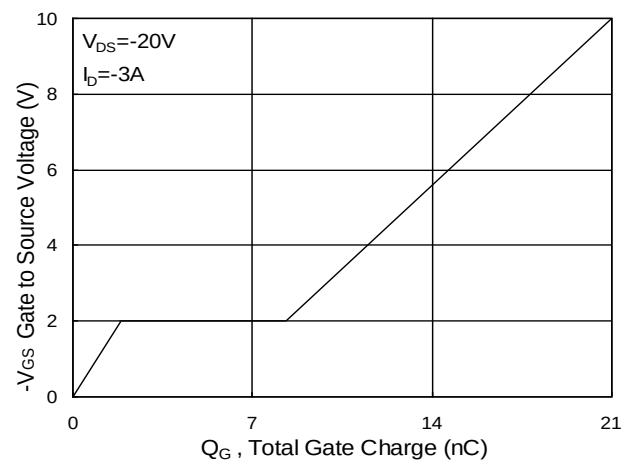


Fig.4 Gate-Charge Characteristics

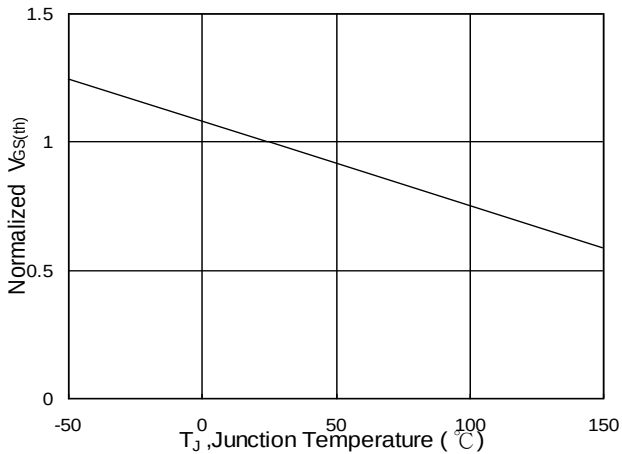


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

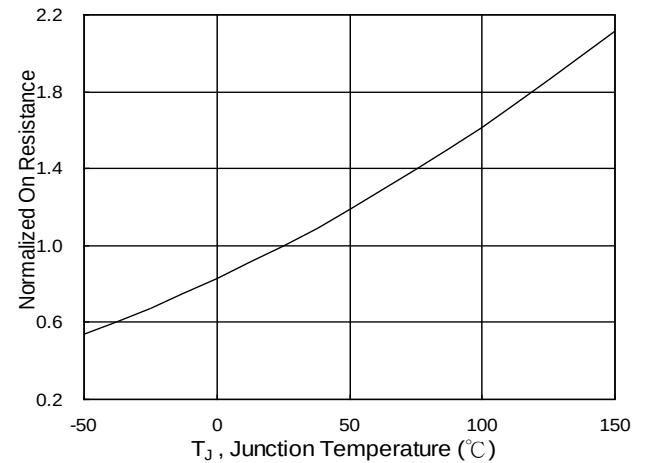


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

P-Channel Typical Characteristics

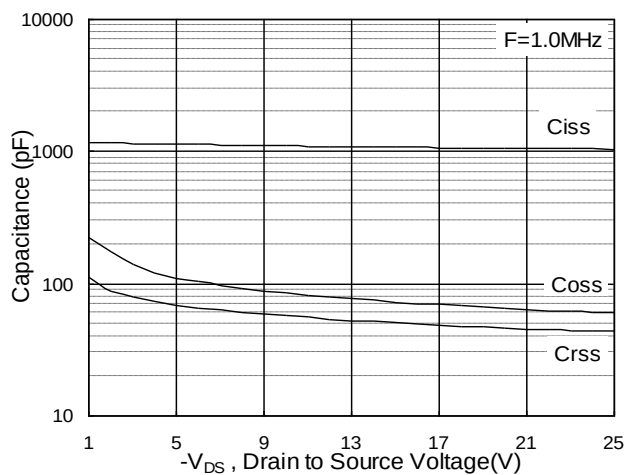


Fig.7 Capacitance

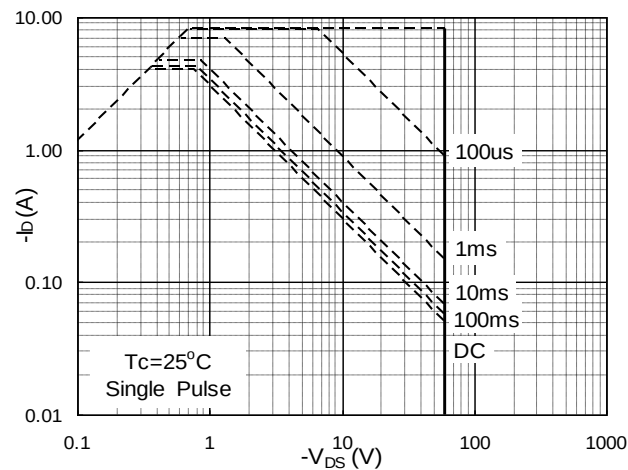


Fig.8 Safe Operating Area

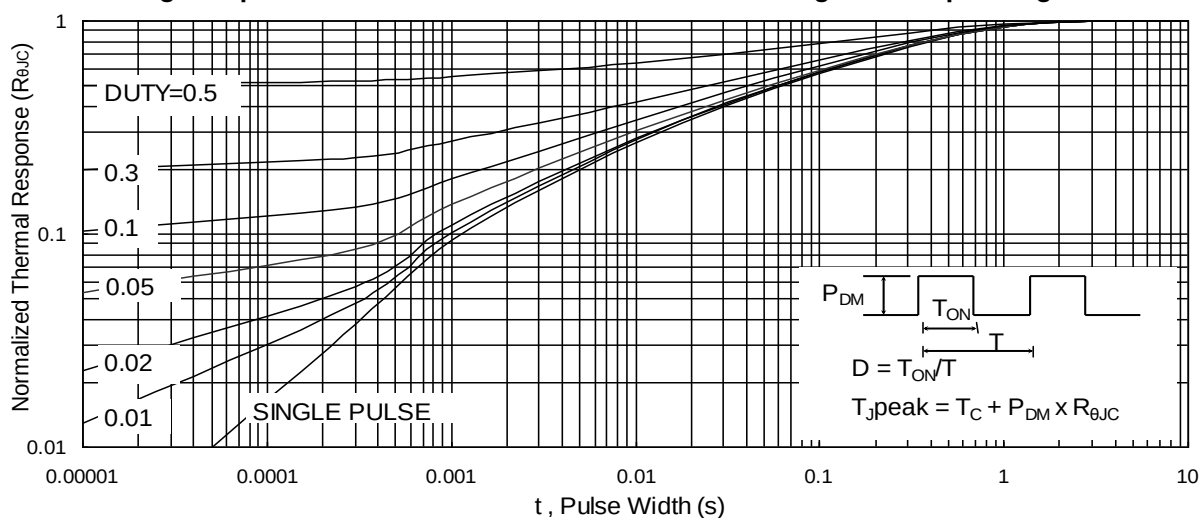


Fig.9 Normalized Maximum Transient Thermal Impedance

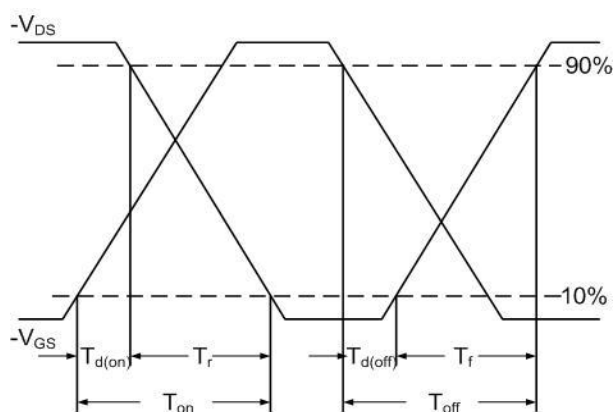


Fig.10 Switching Time Waveform

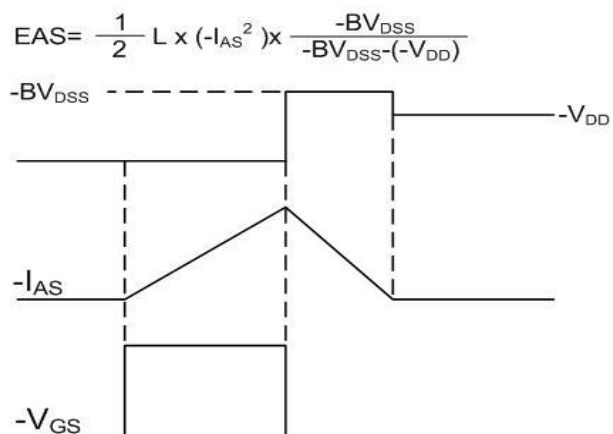
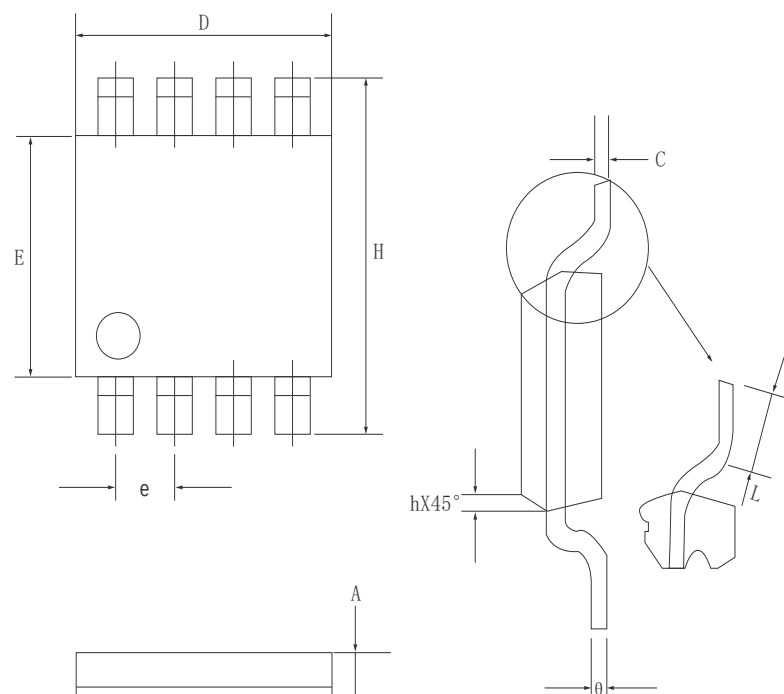
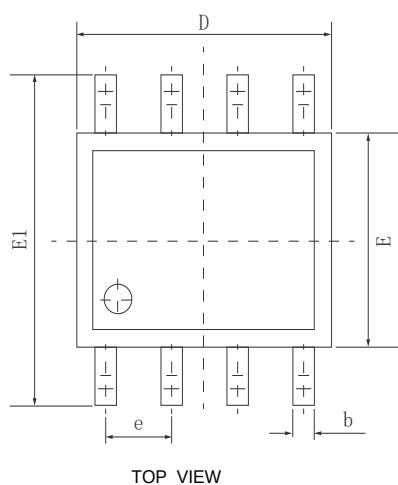
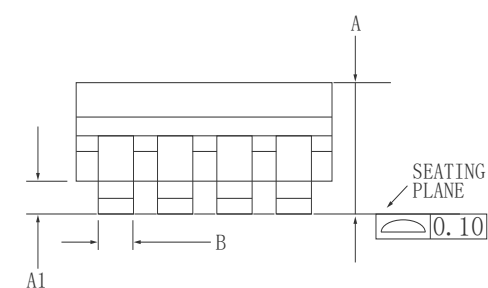


Fig.11 Unclamped Inductive Waveform

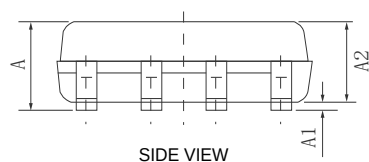
•Dimensions (SOP8)



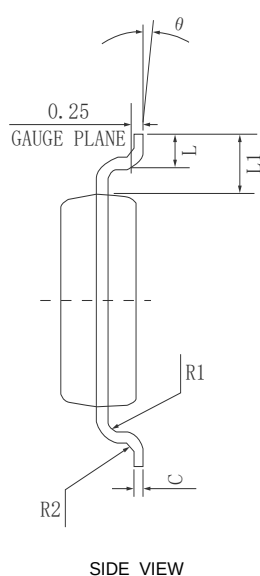
DIM	MILLIMETERS	
	MIN	MAX
A	1.35	1.75
A1	0.02	0.15
B	0.33	0.5
C	0.1	0.25
D	4.8	5
E	3.8	4
e	1.27 (BSC)	
H	5.8	6.2
h	0.25	0.5
I	0.4	1.25
θ	0°	7°



TOP VIEW



SIDE VIEW

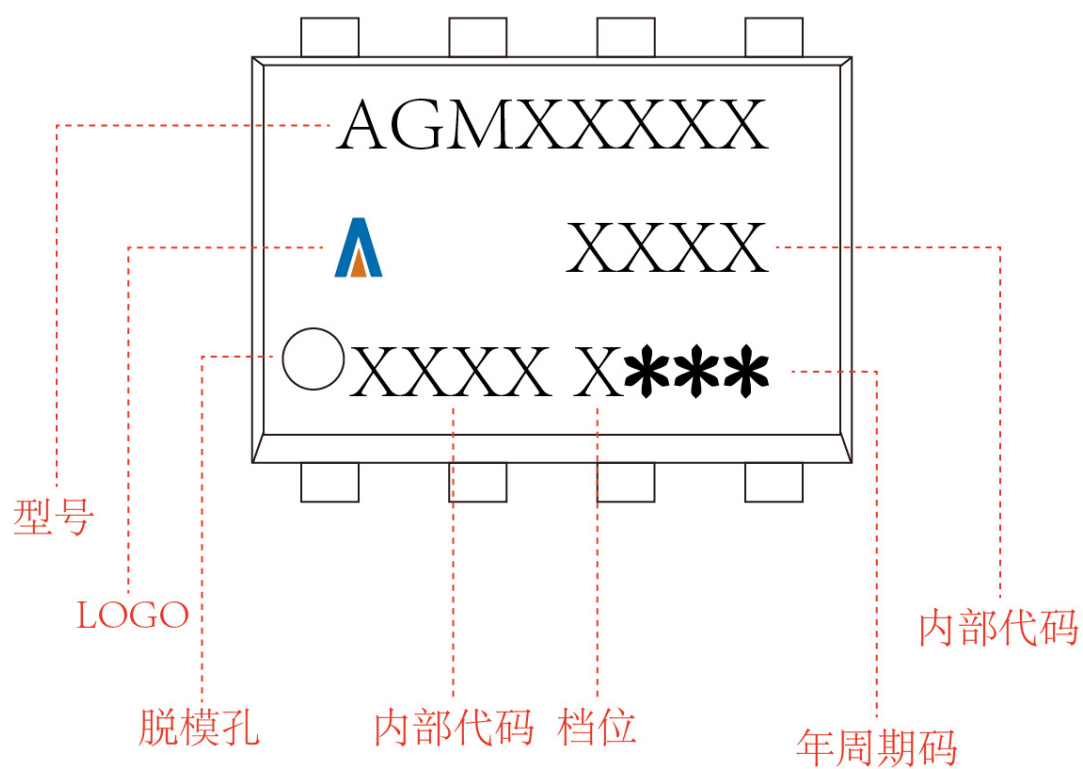


SIDE VIEW

SYMBOL	MIN	NOM	MAX
A	1.40	1.60	1.80
A1	0.05	0.15	0.25
A2	1.35	1.45	1.55
b	0.30	0.40	0.50
c	0.153	0.203	0.253
D	4.80	4.90	5.00
E	3.80	3.90	4.00
E1	5.80	6.00	6.20
L	0.45	0.70	1.00
θ	2°	4°	6°
L1	1.04 REF		
e	1.27 BSC		
R1	0.07 TYP		
R2	0.07 TYP		

SOP8

Marking Instructions:



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